IN THE SPECIFICATION

Please amend the paragraph starting at page 13, line 19 and ending at page 16, line 20 as follows:

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a graph showing a Vf-log(Ie) characteristic, aiding in describing the irreversible characteristic of an electron-emitting device according to Embodiment 1 of the invention;

Fig. 2 is a schematic view showing one example of the electron-emitting device according to Embodiment 1 of the invention;

Figs. 3A to 3C are cross-sectional schematic views showing a method of fabricating a cathode electrode and an electron-emitting device on the cathode electrode;

Fig. 4 is a graph showing the I-V characteristic of the electron-emitting device;

Fig. 5 is a graph showing the F-N characteristic of the electron-emitting device;

Fig. 6A is a schematic top plan view of the electron-emitting device which uses an aggregate of carbon fibers provided with a gate electrode, as its electron-emitting member;

Fig. 6B is a cross-sectional view taken along line A-A of Fig. 6A;

Fig. 7 is a schematic view aiding in describing the state in which electrons emitted from the electron-emitting device move toward an anode electrode;

Fig. 8 is a graph showing the Vf-Ie characteristic of the electron-emitting device;

Fig. 9 is a graph showing the Vf-log(Ie) characteristic of the electron-emitting device;

Fig. 10 is a graph showing the 1/Vf-log(Ie/Vf^2) characteristic of the electron-emitting device;

Fig. 11 is a graph showing the log(t)-Ie(normalized) characteristic of the electron-emitting device;

Fig. 12 is a graph showing the 1/Vf-log(Ie/Vf^2) characteristic, aiding in describing the irreversible characteristic of the electron-emitting device according to Embodiment 2;

Fig. 13 is a graph showing the 1/Vf-log(Ie/Vf^2) characteristic of an electron-emitting device using carbon nanotubes (CNT) and graphite nanofibers (GNF) as its electron-emitting member;

Fig. 14 is a schematic plan view of a multi-electron source in which electron-emitting devices are disposed in matrix form;

Fig. 15 is a cross-sectional view of the multi-electron source, taken along line A-A' of Fig. 14;

Fig. 16 is a schematic cross-sectional view aiding in describing the states of voltages to be applied during the driving of the multi-electron source;

Fig. 17 is a graph comparatively showing different 1/Vf-log(Ie/Vf^2) characteristics of different electron-emitting devices;

Fig. 18 is a graph comparatively showing different 1/Vf-log(Ie/Vf^2) characteristics for the purpose of describing a method of uniformizing the electron emission characteristics of different electron-emitting devices according to Embodiment 3 of the invention;

Fig. 19 is a graph comparatively showing different 1/Vf-log(Ie/Vf^2) characteristics for the purpose of describing a characteristic shift voltage applying step;

Fig. 20 is a graph comparatively showing different 1/Vf-log(Ie/Vf^2) characteristics for the purpose of describing a reference device voltage adjusting step;

Figs. 21A to 21D are schematic cross-sectional views aiding in describing a process of manufacturing the electron-emitting device;

Fig. 22 is a graph showing the F-N characteristic of an electron-emitting device according to Example 2;

Fig. 23 is a schematic view of a multi-electron source;

Figs. 24A to 24C are schematic views showing one example of the form of carbon fibers;

Figs. ~~25A to 25C~~ 25A to 25D are schematic views showing another example of the form of carbon fibers; and

Fig. 26 is a schematic view showing one example of an electron-emitting device.